



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D MAX T _A = +25°C
	17mΩ @ V_{GS} = -10V	-8.6A
-30V	25mΩ @ V _{GS} = -4.5V	-7.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

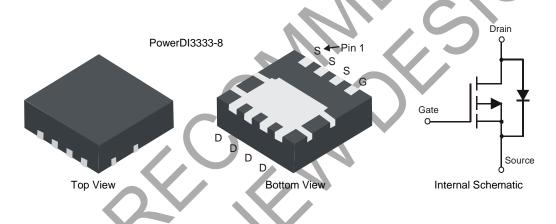
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDl[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging			
DMP3008SFG-7	PowerDI3333-8	2000/Tape & Reel			
DMP3008SFG-13	PowerDI3333-8	3000/Tape & Reel			
Notes: 1. No purposely added lead, Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.					

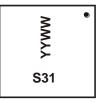
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



S31 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



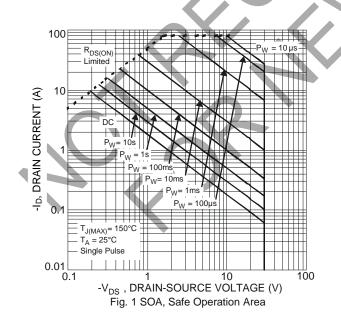
Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

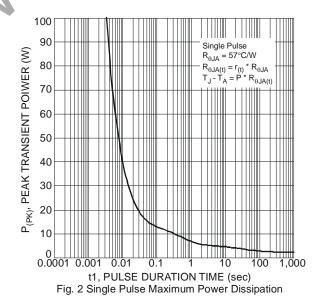
Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-8.6 -7.0	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$	t<10s $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	-11.7 -9.3	А
Continuous Drain Current (Note C) // 45/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-7.1 -5.6	А
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-9.6 -7.6	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	А
Maximum Continuous Body Diode Forward Current (Note 6)			IS	-3.0	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		140	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	R _{0JA}	72	°C/W
Total Power Dissipation (Note 6)		PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		57	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R ₀ JA	30	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	7.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

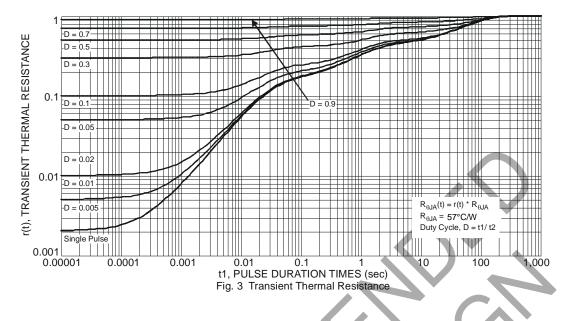
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.







NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3036SFV</u>



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

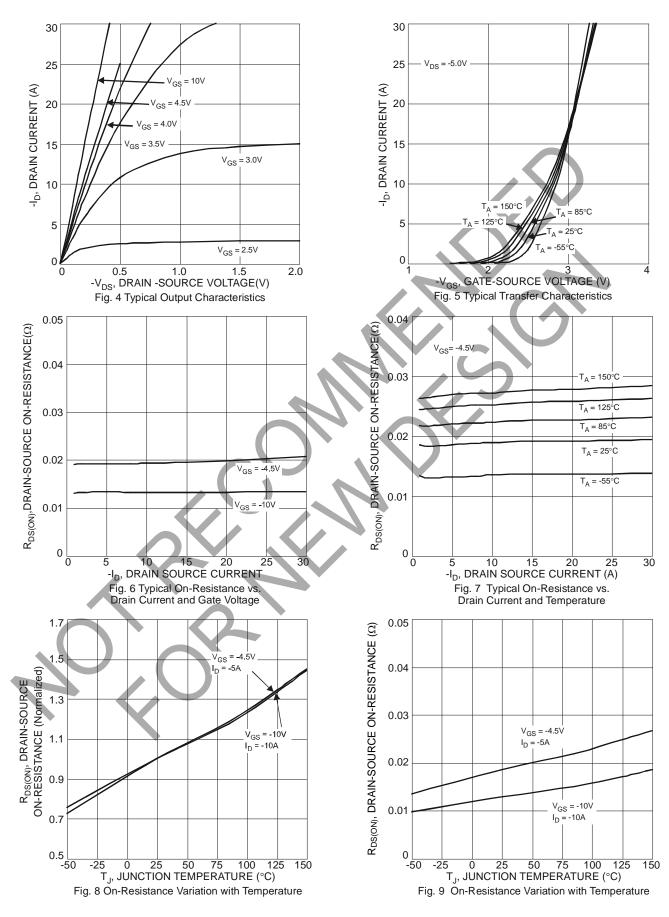
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	B V _{DSS}	-30	—		V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	lgss			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance			12.5	17	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		18.5	25	1115.2	$V_{GS} = -4.5V, I_D = -10A$	
Forward Transfer Admittance	Y _{fs}		13	_	S	$V_{DS} = -15V, I_{D} = -10A$	
Diode Forward Voltage	Vsd		-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2230	—			
Output Capacitance	Coss		328		pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	—	294	—			
Gate Resistance	Rg		6.4	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -10V)	Qg	_	47	—			
Total Gate Charge (V _{GS} = -4.5V)	Qg		23	—	nC		
Gate-Source Charge	Q _{gs}	_	9.4			$V_{DS} = -15V, I_D = -10A$	
Gate-Drain Charge	Q _{qd}	_	5.6				
Turn-On Delay Time	t _{D(ON)}		10.5				
Turn-On Rise Time	t _R		8.5			$V_{GS} = -10V, V_{DS} = -15V, R_g = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}		90		ns		
Turn-Off Fall Time	t _F		40		1		

Notes: 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.



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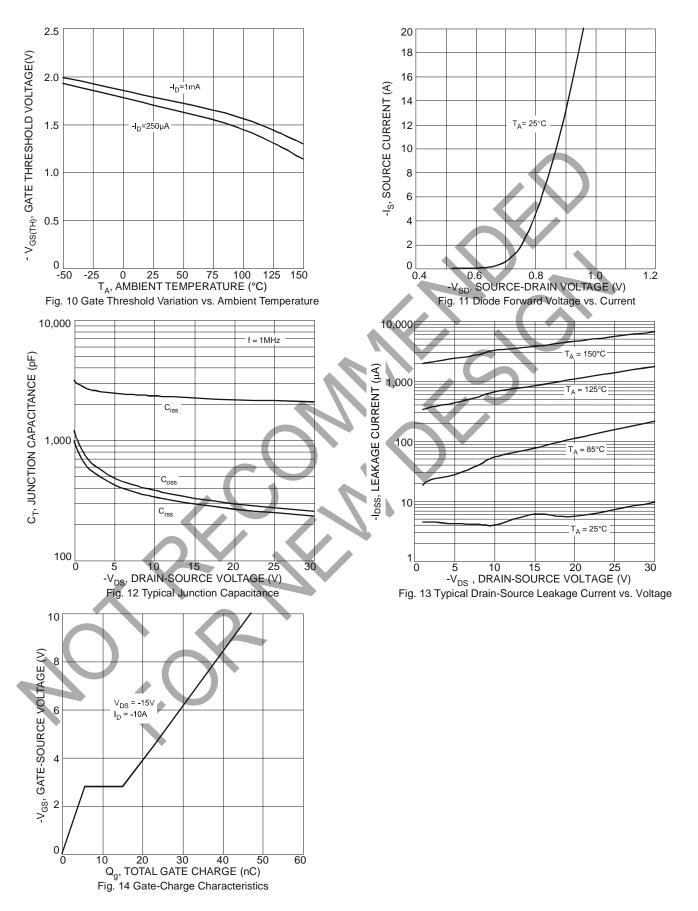
DMP3008SFG





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DMP3008SFG

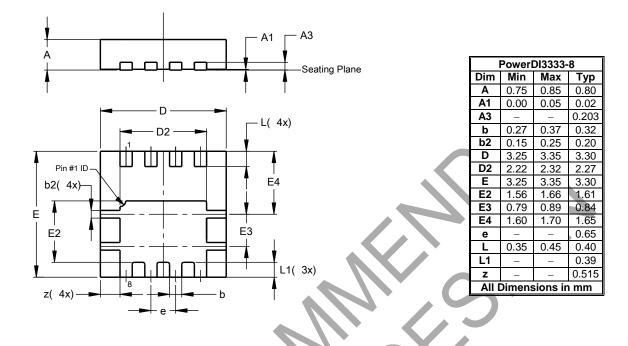




Package Outline Dimensions

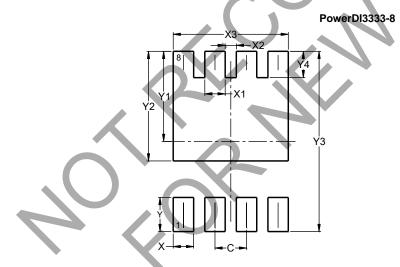
Please see http://www.diodes.com/package-outlines.html for the latest version.





Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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